

# isc Silicon NPN Power Transistor

### **DESCRIPTION**

- · Collector-Emitter Breakdown Voltage-
  - : V<sub>(BR)CEO</sub>= 250V(Min)
- High Collector Power Dissipation
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

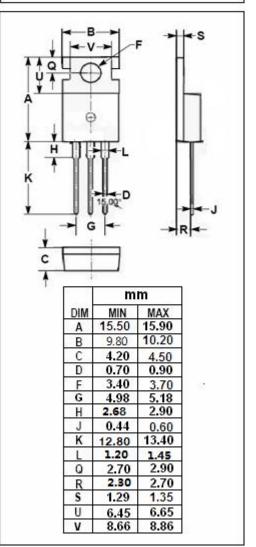
# PIN 1. BASE 2.COLLECTOR 3. BMITTER 1 2 3 TO-220C package

### **APPLICATIONS**

• Designed for AF power amplifier applications.

# ABSOLUTE MAXIMUM RATINGS(T<sub>a</sub>=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	350	V
V <sub>CEO</sub>	Collector-Emitter Voltage	250	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
Ic	Collector Current-Continuous	1	А
Ісм	Collector Current-Peak	2	Α
Pc	Collector Power Dissipation @ T <sub>C</sub> =25℃	40	W
TJ	T <sub>J</sub> Junction Temperature		${\mathbb C}$
T <sub>stg</sub>	T <sub>stg</sub> Storage Temperature Range		$^{\circ}$





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2SD860

### **ELECTRICAL CHARACTERISTICS**

Tc=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT	
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 10mA; I <sub>B</sub> = 0	250			V	
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 2A; I <sub>B</sub> = 0.4A			1.0	V	
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = 2A; V <sub>CE</sub> = 10V			1.5	V	
I <sub>CEO</sub>	Collector Cutoff Current	V <sub>CE</sub> = 150V; I <sub>B</sub> = 0			1	mA	
I <sub>CES</sub>	Collector Cutoff Current	V <sub>CE</sub> = 350V; V <sub>BE</sub> = 0			1	mA	
I <sub>ЕВО</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			1	mA	
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 0.3A; V <sub>CE</sub> = 10V	40		250		
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 2A; V <sub>CE</sub> = 10V	10				
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.2A; V <sub>CE</sub> = 5V;		20		MHZ	
Switching Times							
t <sub>on</sub>	Turn-On Time			0.2		μ <b>S</b>	
t <sub>off</sub>	Turn-Off Time	I <sub>C</sub> = 2A; I <sub>B1</sub> = I <sub>B2</sub> = 0.2A		2.0		μs	

# ♦ h<sub>FE-1</sub> Classifications

R	Q	Р
40-90	70-150	120-250

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